

## **AMENDMENT TO THE CLAIMS**

### **Listing Of All Claims**

1. (original) A method of forming a bond pad, the method comprising:
  - a) depositing a dielectric layer on a substrate;
  - b) depositing a photoresist layer on the dielectric layer;
  - c) forming an etch mask in the photoresist layer wherein the mask includes (1) a first mask section for etching a bond pad hole and (2) a second mask section for etching a trench, wherein the first and second mask sections are contiguous;
  - d) etching the first and second mask sections through the dielectric layer, wherein a bond pad hole and a contiguous trench are formed, such that the bond pad hole and the trench expose a section of the substrate; and
  - e) forming a layer comprising Cu, in the pad hole and in the trench, wherein a bond pad having a contiguous interconnect line is formed.
2. (original) The method of claim 1 additionally comprising:
  - a) depositing a passivation layer on (1) the dielectric layer, (2) the bond pad and (3) the contiguous interconnect line; and
  - b) forming a passivation hole through the passivation layer such that the passivation hole exposes at least a portion of the bond pad.
3. (original) The method of claim 1 wherein the substrate comprises a top layer including a C-doped silicon oxide material.
4. (original) The method of claim 3 wherein the C-doped silicon oxide material comprises an oxidized organo silane material including an oxidized organo silane compound that is formed by reacting an organo silane compound with an oxidizing compound.
5. (original) The method of claim 4 wherein the oxidized organo silane material comprises a carbon content of at least 1% by atomic weight.

6. (original) The method of claim 5 wherein the oxidized organo silane material is formed by reacting an organo silane compound with  $\text{N}_2\text{O}$  gas at plasma conditions sufficient to form the layer and wherein the plasma conditions additionally comprise:
  - a) a high frequency RF power density ranging from about  $0.16 \text{ W/cm}^2$  to about  $0.48 \text{ W/cm}^2$  for forming the layer; and
  - b) a sufficient amount of organo silane compound with respect to the  $\text{N}_2\text{O}$  gas to form the layer.
7. (original) The method of claim 5 wherein the oxidized organo silane material is formed by reacting an organo silane compound with  $\text{O}_2$  gas at plasma conditions sufficient to form the layer and wherein the plasma conditions comprise:
  - a) a high frequency RF power density greater than about  $0.03 \text{ W/cm}^2$  for forming the layer; and
  - b) a sufficient amount of organo silane compound with respect to the  $\text{O}_2$  gas to form the layer.
8. (original) The method of claim 1 wherein the substrate comprises an IC structure.
9. (original) The bond pad formed according to the method of claim 2.

10-40 (cancelled)